



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN#20260422001.2

**Qualification of RFAB as an additional Fab site, CD-PR as additional wafer probe site, Die Revision, Datasheet update and TI Chengdu as additional Assembly/Test site options for select devices
Change Notification / Sample Request**

Date: April 22, 2026

To: MOUSER PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

Texas Instruments requires acknowledgement of receipt of this notification within 60 days of the date of this notice. Lack of acknowledgement of this notice within 60 days constitutes acceptance and approval of this change. If samples or additional data are required, requests must be received within 60 days of this notification.

The changes discussed within this PCN will not take effect any earlier than the proposed first ship date on Page 3 of this notification, unless customer agreement has been reached on an earlier implementation of the change.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice or to provide acknowledgement of this PCN, you may contact your local Field Sales Representative or the change management team.

For sample requests or sample related questions, contact your local Field Sales Representative.

TI values customer engagement and feedback related to TI changes. Customers should contact TI if there are questions or concerns regarding a change notification.

Sincerely,

Change Management Team
SC Business Services

20260422001.2
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, you have recently purchased these devices. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
TPS79501QDRBRQ1	NULL

Technical details of this Product Change follow on the next page(s).

PCN Number:	20260422001.2	PCN Date:	April 22, 2026																				
Title:	Qualification of RFAB as an additional Fab site, CD-PR as additional wafer probe site, Die Revision, Datasheet update and TI Chengdu as additional Assembly/Test site options for select devices																						
Customer Contact:	Change Management Team	Dept:	Quality Services																				
Proposed 1st Ship Date:	October 19, 2026	Sample requests accepted until:	June 21, 2026*																				
*Sample requests received after June 21, 2026 will not be supported.																							
Change Type:																							
☒ Assembly Site	☒ Design	☐ Wafer Bump Material																					
☒ Assembly Process	☒ Data Sheet	☐ Wafer Bump Process																					
☒ Assembly Materials	☐ Part number change	☒ Wafer Fab Site																					
☐ Mechanical Specification	☒ Test Site	☒ Wafer Fab Material																					
☒ Packing/Shipping/Labeling	☐ Test Process	☒ Wafer Fab Process																					
PCN Details																							
Description of Change:																							
Texas Instruments is pleased to announce the qualification of RFAB as an additional Fab site option, CD-PR as additional wafer probe site & TI Chengdu as additional Assembly/Test site options for the devices listed below.																							
<table border="1"> <thead> <tr> <th colspan="3">Current Fab Site</th> <th colspan="3">Additional Fab site</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>DL-LIN</td> <td>LBC3</td> <td>200mm</td> <td>RFAB</td> <td>LBC9</td> <td>300mm</td> </tr> </tbody> </table>						Current Fab Site			Additional Fab site			Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter	DL-LIN	LBC3	200mm	RFAB	LBC9	300mm
Current Fab Site			Additional Fab site																				
Current Fab Site	Process	Wafer Diameter	Additional Fab site	Process	Wafer Diameter																		
DL-LIN	LBC3	200mm	RFAB	LBC9	300mm																		
The die was also changed as a result of the process change.																							
Wafer Probe Test:																							
<table border="1"> <thead> <tr> <th></th> <th>Current</th> <th>Proposed</th> </tr> </thead> <tbody> <tr> <td>Wafer probe test</td> <td>DL-MOS-4 (TI Dallas Probe)</td> <td>CD-PR (TI Chengdu Probe)</td> </tr> </tbody> </table>							Current	Proposed	Wafer probe test	DL-MOS-4 (TI Dallas Probe)	CD-PR (TI Chengdu Probe)												
	Current	Proposed																					
Wafer probe test	DL-MOS-4 (TI Dallas Probe)	CD-PR (TI Chengdu Probe)																					
Construction differences are as follows:																							
<table border="1"> <thead> <tr> <th></th> <th>Additional site</th> <th></th> </tr> </thead> <tbody> <tr> <td>Assembly & Test site</td> <td>TI Malyasia</td> <td>TI Chengdu</td> </tr> <tr> <td>Wire bond diam/type</td> <td>1.98 mil Cu</td> <td>1 mil Cu</td> </tr> <tr> <td>Mold compound</td> <td>4208625</td> <td>4222198</td> </tr> <tr> <td>MSL</td> <td>LVL3-260C</td> <td>LVL2-260C</td> </tr> </tbody> </table>							Additional site		Assembly & Test site	TI Malyasia	TI Chengdu	Wire bond diam/type	1.98 mil Cu	1 mil Cu	Mold compound	4208625	4222198	MSL	LVL3-260C	LVL2-260C			
	Additional site																						
Assembly & Test site	TI Malyasia	TI Chengdu																					
Wire bond diam/type	1.98 mil Cu	1 mil Cu																					
Mold compound	4208625	4222198																					
MSL	LVL3-260C	LVL2-260C																					
The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history. The links to the revised datasheets are available in the table below.																							

Changes from Revision * (September 2010) to Revision A (February 2026)	Page
• Updated the number formatting for tables, figures, and cross-references throughout the document.....	1
• Added references for the new chip throughout the document.....	1
• Added the <i>Pin Configurations and Functions</i> section.....	3
• Added Recommended Operating Conditions table.....	5
• Added new chip plots to <i>Typical Characteristics</i> sections.....	7
• Added the <i>Feature Description</i> section.....	14
• Added the <i>Device Functional Modes</i> section.....	17
• Added the <i>Application and Implementation</i> section.....	18
• Added the <i>Power Supply Recommendations</i> section.....	20
• Added the <i>Layout</i> section.....	20
• Added the <i>Device and Documentation Support</i> section.....	23
• Added the <i>Mechanical, Packaging, and Orderable Information</i> section.....	24

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
TPS79501-Q1	SLVSAJ9	SLVSAJ9A	http://www.ti.com/product/TPS79501-Q1

Changes between new and legacy devices are labeled in the datasheet as legacy chip (LBC3) and new chip (LBC9), respectively. An example of that comparison is shown below:

5.5 Electrical Characteristics

at operating temperature range ($T_J = -40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$), $V_{EN} = V_{IN}$, $V_{IN} = V_{OUT(nom)} + 1\text{V}^{(1)}$, $I_{OUT} = 1\text{mA}$, and $C_{OUT} = 10\mu\text{F}$ and $C_{NR} = 0.01\mu\text{F}$ (Legacy Chip only), unless otherwise noted. All typical values at $T_J = 25^{\circ}\text{C}$.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IN}	Input Voltage	Legacy chip	2.7	5.5	V
		New chip	2.7	6.0	

8.1.2 Device Nomenclature

Table 8-1. Available Options

PRODUCT	DESCRIPTION
TPS79501Qyyy zM3Q1	01 denotes that this is an adjustable output voltage device. Q indicates that this device is a Grade-1 device in accordance with the AEC-Q100 standard. yyy is the package designator. z is the package quantity. M3 is a suffix designator for the devices that only use the latest manufacturing flow (CSO:RFB). Devices without this suffix ship with the legacy chip (CSO:DLN) or the new chip (CSO:RFB). The reel packaging label provides CSO information to distinguish which chip is used. Q1 indicates that this device is an automotive grade (AEC-Q100) device.

Qual details are provided in the Qual Data Section.

Test coverage, insertions, conditions will remain consistent with current testing.

Reason for Change:

New wafer fab (RFAB) which results in the process change to LBC9 and assembly BOM change. Assembly site change/addition is included to support 300mm wafers.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

Review the SDP for full evaluation of the change based on the customer use case.

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS

☒ No Change

REACH

☒ No Change

Green Status

☒ No Change

IEC 62474

☒ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
RFAB	RFB	USA	Richardson

Die Rev:

Current

New

Die Rev [2P]	Die Rev [2P]
A	A

Assembly Site Information:

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
Malaysia	MLA	MYS	Kuala Lumpur
TI Chengdu	CU3	CHN	Chengdu

Sample product shipping label (not actual product label):



Product Affected:

TPS79501QDRBRQ1

Automotive Qualification Summary
(As per AEC-Q100 Rev. J and JEDEC Guidelines)

Approve Date 08-February -2026

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS79501QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS78550QWDRBRQ1	QBS Package Reference: TPS78550QWDRCRQ1
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Test Group A - Accelerated Environment Stress Tests

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS79501QDRBRM3Q1	QBS Package Reference: CAXC8T245QRHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS78550QWDRBRQ1	QBS Package Reference: TPS78550QWDRCRQ1
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	-	-	3/All/0	-	-	-
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	-	-	-	1/All/0	3/All/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	-	-	1/77/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	3/231/0	-	-	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	-	-	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	-	1/77/0	1/77/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	3/9/0	-	1/5/0	1/3/0
PTC	A5	JEDEC JESD22-A105	1	45	PTC	-40/125C	1000 Cycles	-	-	-	1/45/0	1/45/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	-	-	1/77/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	1/45/0	-

Test Group B - Accelerated Lifetime Simulation Tests

HTOL	B1	JEDEC JESD22-A108	3	77	Life Test	125C	1000 Hours	-	-	3/231/0	1/77/0	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	-
EDR	B3	AEC Q100-005	1	77	NVM Endurance, Data Retention, and Op Life	Per QSS-009-018	1 Step	-	-	3/231/0	-	-

Test Group C - Package Assembly Integrity Tests

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device TPS79501QDRBRM3Q1 is qualified at MSL2 260C

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS79501QDRBRM3Q1	QBS Package Reference: CAXC8T245QBHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS78550QWDRBRQ1	QBS Package Reference: TPS78550QWDRCRQ1
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	-	1/30/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	-	1/30/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-	-	-	1/15/0
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	1/15/0
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-	1/10/0	3/30/0
Test Group D - Die Fabrication Reliability Tests												
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDD	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
BTI	D4	-	-	-	Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests												
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	-	-	1/3/0	-
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	-	-	1/3/0	-
LU	E4	AEC Q100-004	1	3	Latch-Up	Per AEC Q100-004	-	1/3/0	-	-	1/6/0	-
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TPS79501QDRBRM3Q1	QBS Package Reference: CAXC8T245QBHLRQ1	QBS Process Reference: BQ79600PWRQ1	QBS Product Reference: TPS78550QWDRBRQ1	QBS Package Reference: TPS78550QWDRCRQ1
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	1/30/0	-	-	1/30/0	-
Additional Tests												

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Orderable Part Numbers

The following table contains a list of all TI Orderable Part Numbers (OPNs) released by this qualification per Product Qualification Family definition (AEC Q100 Appendix 1). Group E results shown above cover all part numbers listed here.

TPS79501QDRBRM3Q1

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : ACuHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2412-044

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

**1.0 mil Cu wire in CDAT QFN/SON (10DRC, 8 DRB) Package for LBC9 AI Pad
(Q100H, Grade1, -40/125C)
Approved 27-Jan-2021**

Qualification Results
Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	QBS Package Reference: TPS7B8550QWDRGRQ1	QBS Package Reference: TPS74633PQWDRBRQ1
Test Group A – Accelerated Environment Stress Tests								
PC	A1	-	3	22	SAM Analysis, Pre Stress	Completed	1/22/0	3/66/0
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1- 260C	No fails	No fails
PC	A1	-	3	22	SAM Analysis, Post Stress	Completed	-	3/66/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	1/77/0	3/231/0
HAST	A2	-	3	1	Cross Section, Post bHAST 96 Hours	Completed	1/1/0	3/3/0
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 96 Hours	Wires	1/30/0	3/90/0
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 96 Hours	Wires	1/3/0	3/90/0
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 96 Hours	Wires	1/30/0	3/90/0

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	QBS Package Reference: TPS7B8550QWDRGRQ1	QBS Package Reference: TPS74633PQWDRBRQ1
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	192 Hours	1/77/0	3/231/0
HAST	A2	-	3	1	Cross Section, Post bHAST 192 Hours	Completed	1/1/0	3/3/0
HAST	A2	-	3	22	SAM Analysis, Post bHAST, 192 Hours	Completed	1/22/0	3/66/0
HAST	A2	-	3	30	Wire Bond Shear, Post bHast, 192 Hours	Wires	1/30/0	3/90/0
HAST	A2	-	3	30	Bond Pull over Stitch, post bHAST, 192 Hours	Wires	1/30/0	3/90/0
HAST	A2	-	3	30	Bond Pull over Ball, Post bHAST, 192 Hours	Wires	1/30/0	3/90/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
TC	A4	-	3	1	Cross Section, Post T/C 500 Cycles	Completed	3/3/0	3/3/0
TC	A4	-	3	22	SAM Analysis, Post T/C, 500 Cycles	Completed	3/66/0	3/66/0
TC	A4	-	3	30	Wire Bond Shear, Post T/C 500 Cycles	Wires	3/90/0	3/90/0
TC	A4	-	3	30	Bond Pull over Stitch Post T/C 500 Cycles	Wires	3/90/0	3/90/0
TC	A4	-	3	30	Bond Pull over Ball Post T/C 500 Cycles	Wires	3/90/0	3/90/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	1000 Cycles	3/231/0	3/231/0
TC	A4	-	3	1	Cross Section, Post T/C 1000 Cycles	Completed	3/3/0	3/3/0
TC	A4	-	3	22	SAM Analysis, Post T/C, 1000 Cycles	Completed	3/66/0	3/66/0
TC	A4	-	3	30	Wire Bond Shear, Post T/C 1000 Cycles	Wires	3/90/0	3/90/0
TC	A4	-	3	30	Bond Pull over Stitch, Post T/C, 1000 Cycles	Wires	3/90/0	3/90/0
TC	A4	-	3	30	Bond Pull over Ball, Post T/C, 1000 Cycles	Wires	3/90/0	3/90/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	1000 Cycles	1/45/0	1/45/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle - 40/125C	2000 Cycles	1/45/0	1/45/0
HTSL	A6	JEDEC JESD22-A103	3	45	High Temp Storage Bake 150C	1000 Hours	1/77/0	3/231/0

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	QBS Package Reference: TPS7B8550QWDRGRQ1	QBS Package Reference: TPS74633PQWDRBRQ1
HTSL	A6	-	3	1	Cross Section, Post HTSL 1000 Hours	Completed	1/1/0	3/3/0
HTSL	A6	JEDEC JESD22-A103	3	44	High Temp Storage Bake 150C	2000 Hours	1/77/0	3/231/0
HTSL	A6	-	3	1	Cross Section, Post HTSL 2000 Hours	Completed	1/1/0	3/3/0
Test Group C – Package Assembly Integrity Tests								
WBS	C1	AEC Q100-001	3	30	Wire Bond Shear, Cpk>1.67	Wires	3/90/0	-
WBP	C2	MIL-STD883 Method 2011	3	30	Bond Pull over Ball, Cpk >1.67	Wires	3/90/0	-

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST & TC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40C to +150C

Grade 1 (or Q): -40C to +125C

Grade 2 (or T): -40C to +105C

Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU

Room : AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20181023-127409, 20190619-130350

In performing change qualifications, Texas Instruments follows integrated circuit industry standards in performing defect mechanism analysis and failure mechanism-based accelerated environmental testing to ensure wafer fab process, assembly process and product quality and reliability. As encouraged by these standards, TI uses both product-specific and generic (family) data in qualifying its changes. For devices to be categorized as a 'product qualification family' for generic data purposes, they must share similar product, wafer fab process and assembly process elements. The applicability of generic data (also known at TI as Qualification by Similarity (QBS)) is determined by the Reliability Engineering function following these industry standards. Generic data is shown in the qualification report in columns titled "QBS Process" (for wafer fab process), "QBS Package" (for assembly process) and "QBS Product" (for product family).

ZVEI ID: SEM-DS-01, SEM-DS-02, SEM-DS-03, SEM-DE-01, SEM-DE-02, SEM-DE-03, SEM-PW-02, SEM-PW-03, SEM-PW-09, SEM-PW-13, SEM-PA-08, SEM-PA-11, SEM-PA-14, SEM-PA-18, SEM-PS-04, SEM-PS-02, SEM-TF-01

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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